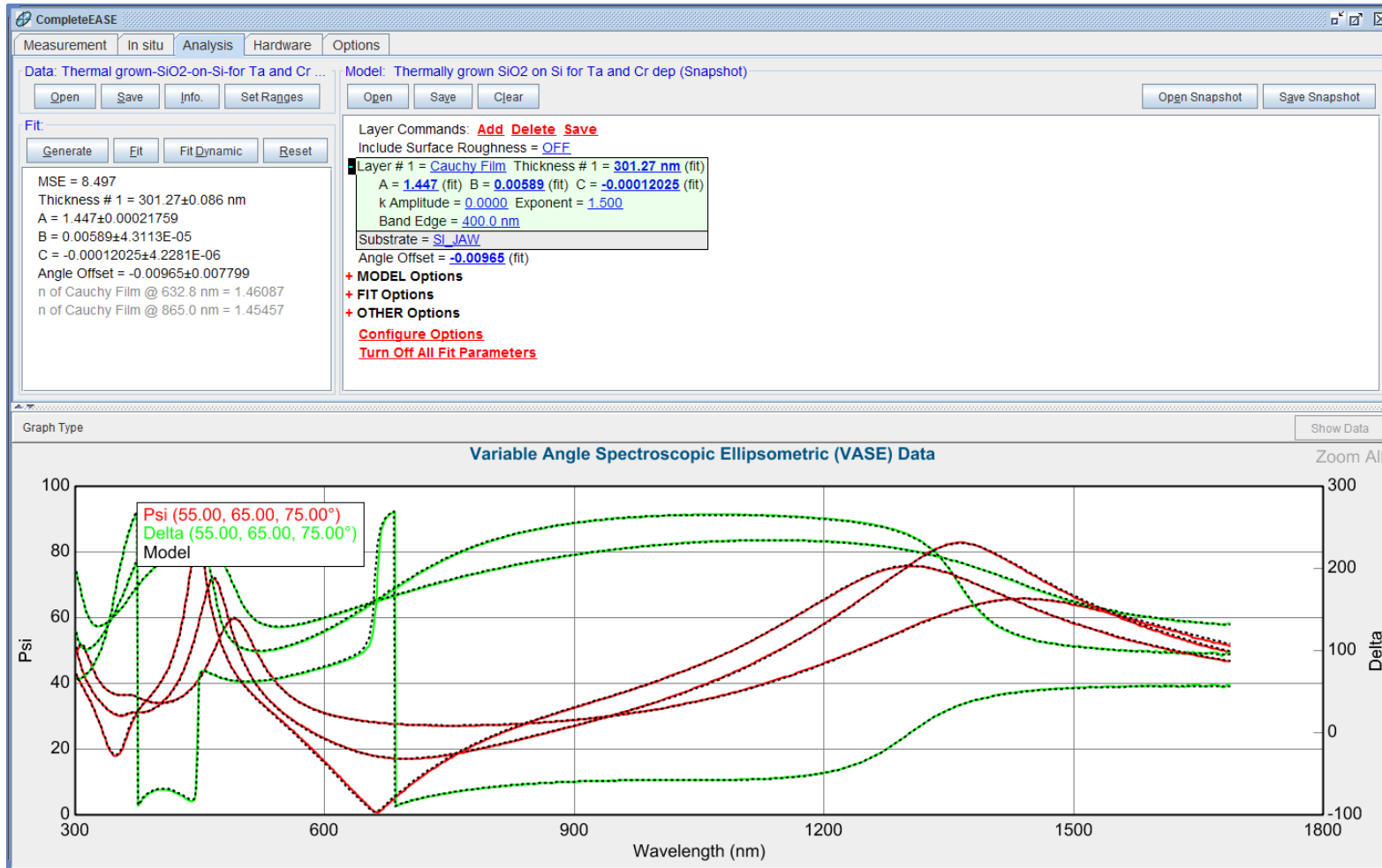


Tantalum and Chromium E-beam Deposition and Wet Etch Testing

Experimental:

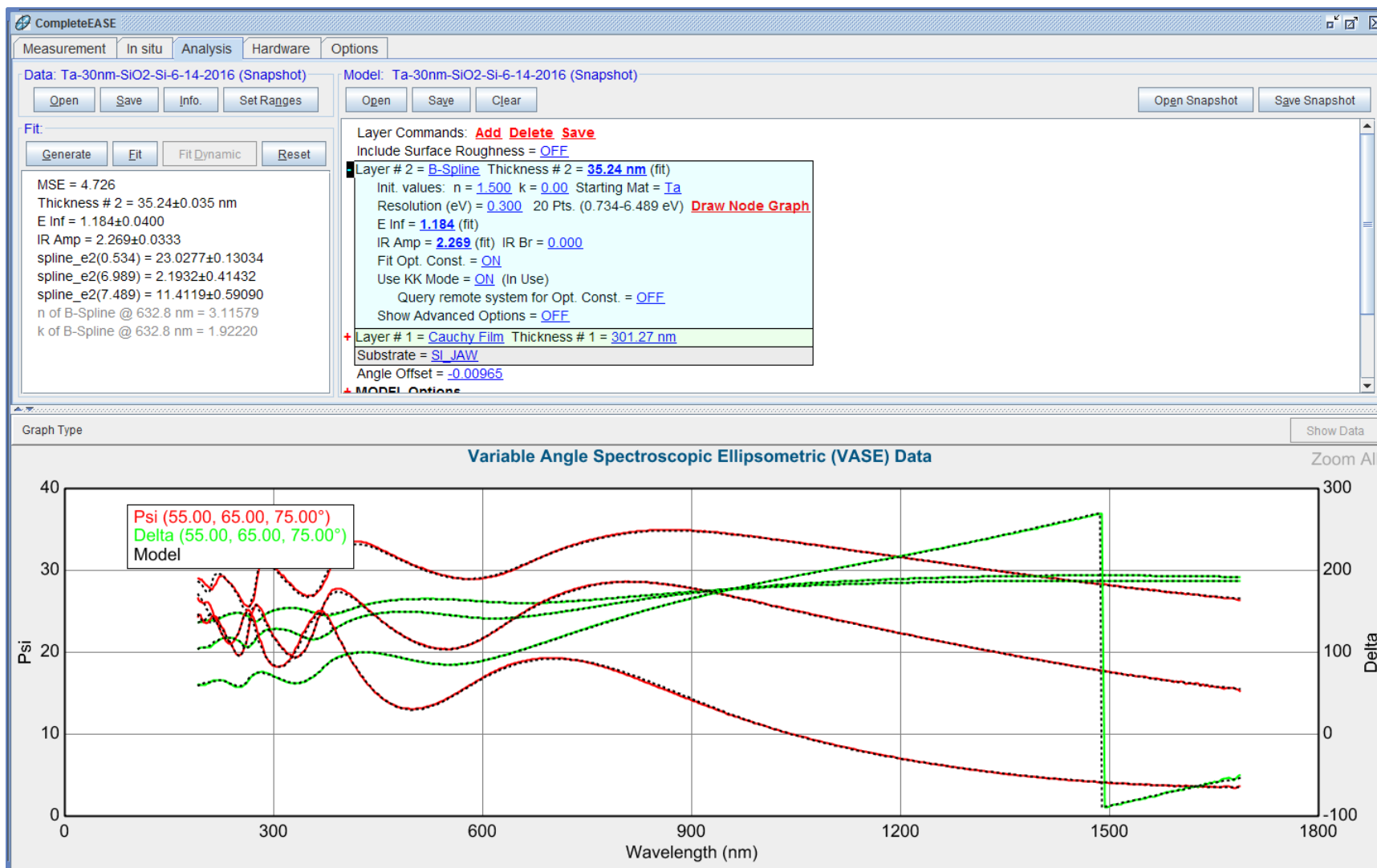
1) Sample: Thermal SiO₂ on one-side polished Si

Ellipsometer:



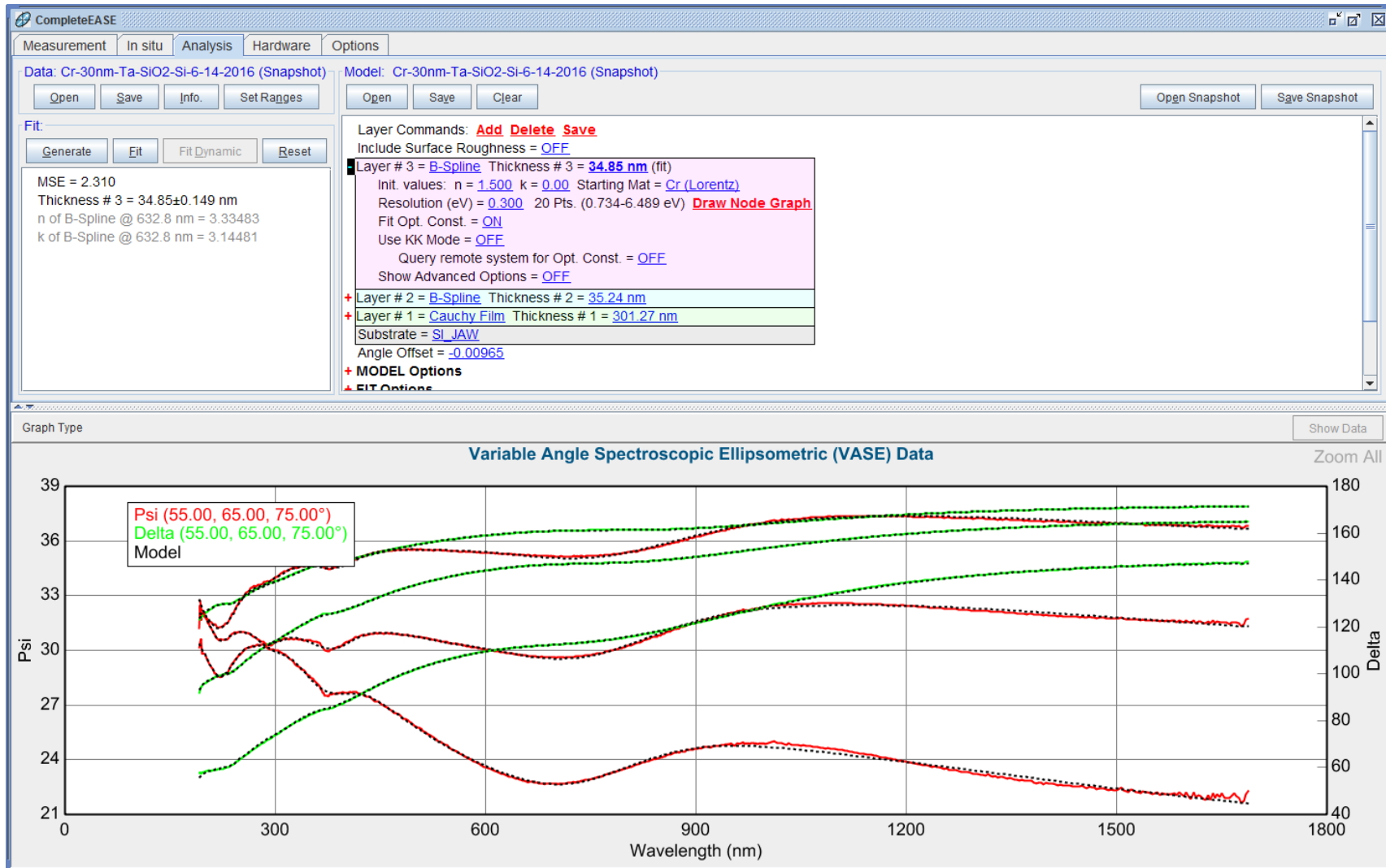
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2) Tantalum deposition using E-beam#1 (Density=16.6 g/cm³; z-Ratio=0.262; Tooling Factor=140; target thickness=30 nm, Rate: 0.5~1.0 Å/s)



Actual Ta thickness=35.24 nm.

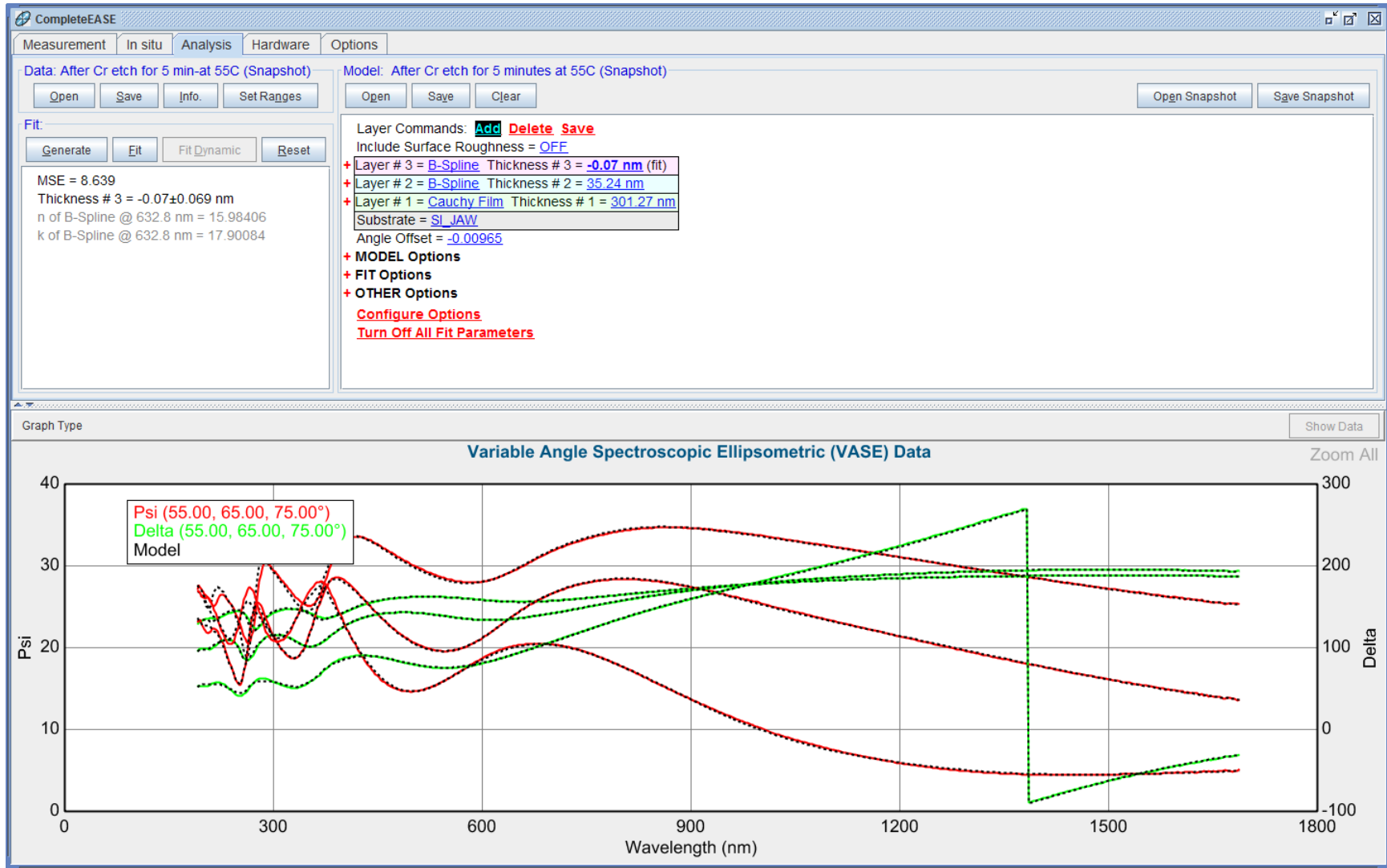
3) Chromium deposition using E-beam#1 (Density=7.2 g/cm³; z-Ratio=0.305; Tooling Factor=140; target thickness=30 nm, Rate: ~2.0 Å/s)



Actual Cr thickness=34.85 nm.

4) Wet Etch of Cr over Ta

Pouring Cr Etchant in glass cup, heat it on a hot plate, set at 55°C, with a glass cover for 1 hour. Etching a sample piece, cut from the whole sample, for 5 minutes. The result: the Cr layer was gone without etching underneath Ta layer.



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Note: Cr etch rate of this etchant is 40 Å/s at 40°C.